Vincent Huc

Diana Dragoe, Régis Guillot Université Paris-Saclay, ICMMO, F91405 Orsay (France) vincent.huc@universite-paris-saclay.fr

The first preparation of graphene by Geim and Novoselov in 2004 sparked an everincreasing interest in 2D materials. Indeed, along with graphene, dichalcogenides such as MoS2 or WS2, silicene, phosphorene, hexagonal boron nitride etc... are also being investigated all over the world, due to their fascinating physical and chemical properties. Besides, the bottom-up synthesis of 2D covalent networks by means of organic synthesis is also being receiving a growing interest. They are usually obtained by assemblying small molecular building units using the rich toolbox of molecular chemistry. We describe here a new process for the synthesis of very high quality 2D materials such a C2N, CN and C4N3 carbon nitrides. This wet process relies on the use of a metallic surface as both a reagent and a support for the coupling of small halogenated building blocks. The conditions of the assembly reaction are chosen so as to leave the inorganic salts by-products on the surface, to further confine the assembly reaction on the surface and increase the quality of the 2D layers. Very high quality flakes are obtained, in terms of lateral size and defect-free nature.

References

A simple and efficient process for the synthesis of 2D carbon nitrides and related materials; Cora Moreira Da Silva et al. Scientific Reports | (2023) 13:15423 | https://doi.org/10.1038/s41598-023-39899-5.

https://cnrs.hal.science/hal-03874253/

Figures





Figure 1: an example of a C4N3 carbon nitride obtained using our new process (A). Optical microscopy (B) and TEM observation (C and D) of C4N3 flakes